

COS10004 Computer Systems

Lecture 4.1: Memory

CRICOS provider 00111D

Dr Chris McCarthy

start:





THIS WEEK:

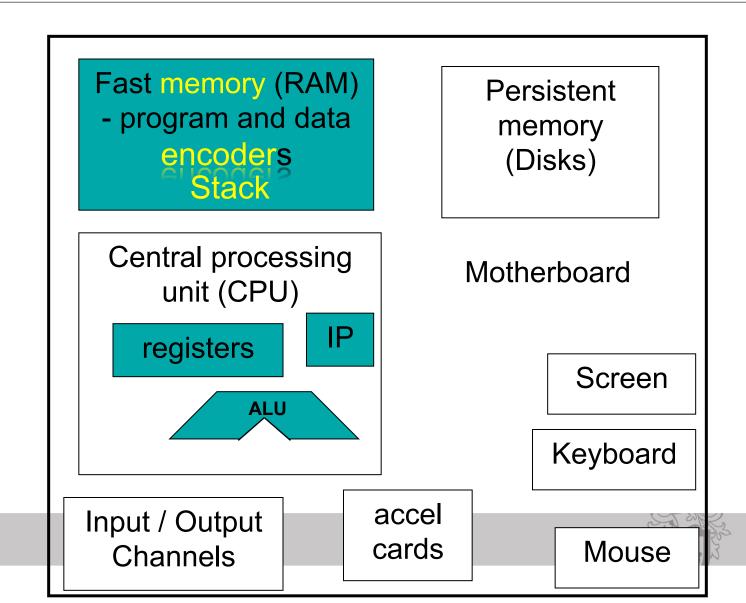
Memory, encoders and stacks

- > Memory different types
- Need encoders/decoders for interrupt handling -
 - 4 to 2 priority encoder used to detect hardware interrupts
 - 2 to 4 used for multiplexing and memory addressing.
- Stacks look like n-dimensional shift registers





Building a computer? Things we need:





ROM (read only memory): All reading at full speed. Just get the address and go there.

- contents built-in at time of manufacture.
- > PROM Programmable read only memory. Programmed by a once-only irreversible operation, e.g. in factory.
- > EPROM Erasable Programmable read only memory. Can be <u>removed</u> from the computer and erased and programmed (slowly) by using special apparatus (e.g. UV light).
 - Sometimes called "field-programmable", i.e. "in the field"
 - Bulk erased: every byte erased at the same time
 - Byte programmable: write bytes one by one.
- > EEPROM Electrically erasable read only memory. Can be erased and reprogrammed byte by byte <u>in situ</u>, but writing is slower than normal reading.





RAM random access memory.

- A misnomer it should be RWM (read write memory) both ROM and RAM allow random access.
- > Static RAM retains information until power removed. Fast, larger area of silicon per byte, modest power requirement.
- > **Dynamic RAM** retains information as long as the contents are refreshed frequently enough. Smaller area of silicon per byte, low power requirement.
 - Does not use flip-flops.
 - Uses tiny capacitors to store electric charge.
 - Because the charge leaks away have to rewrite ("refresh") every few milliseconds.





- > SDRAM (Synchronous DRAM)
 - Hybrid of dynamic and static technology
 - "clocked" by the main CPU clock
- > DDR (double data rate) SDRAM
 - Chips produce data on rising and falling edges of the clock
 - Higher data rates, eg 64 bits / nsec





> FRAM - Ferroelectric RAM

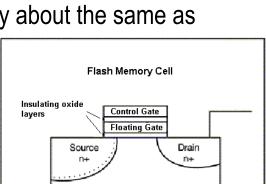
- Uses atom position in unit cell (in theory). Actual density about the same as DRAM. Non-volatile (no power / refresh to keep state).
- Used in specialist devices (where you never want to "turn it off and on again" to fix it). Random access

> Flash memory - (EEPROM)

Charge stored between insulators. Write bit by injecting electrons through a barrier layer (physically damaging it). Used in USB drives. Good for about 30,000 writes. Random access

> Core memory

Magnetic "core" memory: each bit is stored as the direction of magnetisation of tiny rings (like doughnuts).
1955-1975. 1000 x slower than DRAM.



P - Substrate

Kristallstruktur ferroelektrischen Materials PZT (Pb (ZrTi)O3

Electric field

MEMORY ADDRESSING

- > RAM consists of one or many chips
- RAM is organised into words (of e.g. 32 bits)
- Words are grouped into pages.
- Words are selected by an address
 - A number of m bits
- Control bits specify whether to read or write
 - Bits stored in the selected word go to or from

A a byte is typically the smallest addressable chunk of memory. We can address the 4 bytes in a 32-bit word, but we can't address individual bits in each byte. Exceptions include

Micron 3D-XPoint

Address Data bus (m bits) (n bits)





EXAMPLE

- Consider a Computer with 1024 Mbyte (1GB) RAM
 - How many bits needed to address all bytes?

Hint: $1024 = 2^{10}$ and $1,000,000 \sim 2^{20}$

- > Alternative to normal RAM addressing:
 - Hardware stack



LECTURE 4.1 SUMMARY

- Many different types of memory:
 - ROMS variants
 - RAM variants
 - Trade offs of speed, space, expense, longevity
- > All slower to access than registers
- Memory addressing:
 - bits need to address each individual byte (via chip, page, word).



